

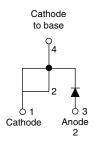
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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 25 A



TO-247AC modified



PRODUCT SUMMARY					
Package	TO-247AC modified (2 pins)				
I _{F(AV)}	25 A				
V _R	600 V				
V _F at I _F	1.7 V				
t _{rr} (yp.	23 ns				
T _J max.	150 °C				
Diode variation	Single die				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)





COMPLIANT
HALOGEN
FREE

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA25PB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25PB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25PB60... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V_{R}		600	V		
Maximum continuous forward current	I _F	T _C = 100 °C	25			
Single pulse forward current	I _{FSM}		225	А		
Maximum repetitive forward current	I _{FRM}		100			
Maximum navar discipation	P _D	T _C = 25 °C	151	W		
Maximum power dissipation		T _C = 100 °C	60			
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C		



VS-HFA25PB60PbF, VS-HFA25PB60-N3

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		600	ı	-	
		I _F = 25 A		-	1.3	1.7	V
Maximum forward voltage	V_{FM}	I _F = 50 A	See fig. 1	-	1.5	2.0	
		I _F = 25 A, T _J = 125 °C		-	1.3	1.7	
Maximum reverse		V _R = V _R rated	Coo fig. 0	-	1.5	20	
leakage current	IRM	I_{RM} $T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \times V_R \text{ rated}$ See fig. 2		-	600	2000	μA
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	55	100	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	12	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	0 A/μs, V _R = 30 V	-	23	-		
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C	I _F = 25 A dI _F /dt = 200 A/µs V _R = 200 V	-	50	75	ns	
366 lig. 3, 10	t _{rr2}	T _J = 125 °C		-	105	160		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	10	А	
See fig. 6, 10	I _{RRM2}	T _J = 125 °C		-	8.0	15		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	112	375	nC	
See fig. 7, 10	Q _{rr2}	T _J = 125 °C		-	420	1200		
Peak rate of fall of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	250	ı	- A/μs	
See fig. 8, 10	dI _{(rec)M} /dt2	T _J = 125 °C		_	160	-		

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	0.83		
Thermal resistance, junction to ambient	R _{thJA}	nJA Typical socket mount		-	40	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-		
Weight			-	6.0	-	g	
Weight			-	0.21	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf ·cm (lbf ·in)	
Marking device		Case style TO-247AC modified (JEDEC)	HFA25PB60				

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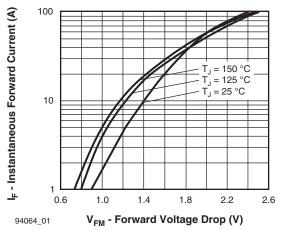


Fig. 1 - Maximum Forward Voltage Drop vs.
Instantaneous Forward Current

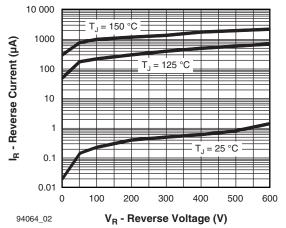


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

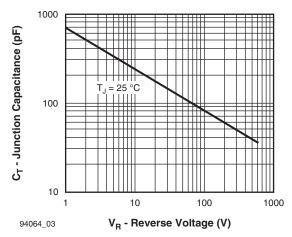


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

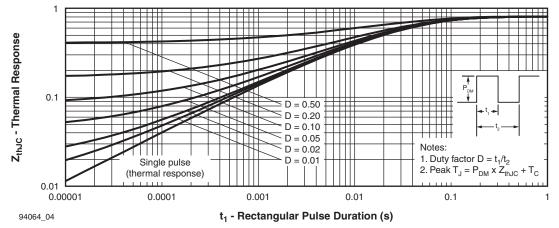


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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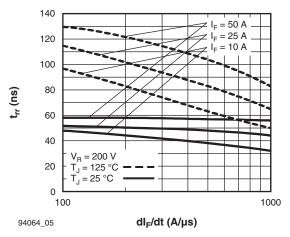


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

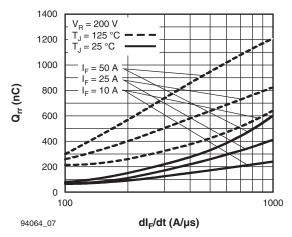


Fig. 7 - Typical Stored Charge vs. dI_F/dt

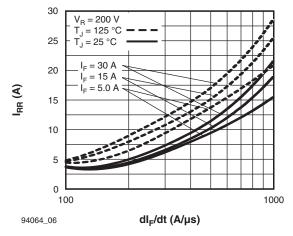


Fig. 6 - Typical Recovery Current vs. dI_F/dt

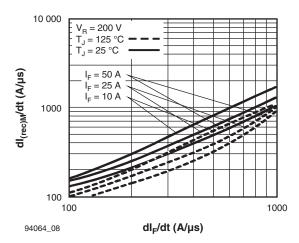


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

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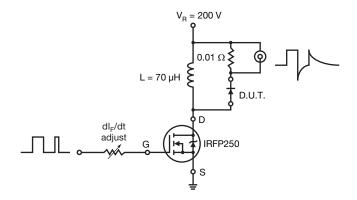
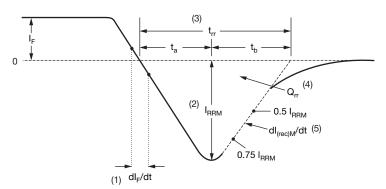


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

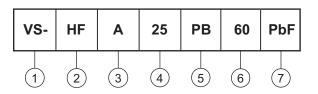
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-HFA25PB60PbF, VS-HFA25PB60-N3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

- HEXFRED® family

Electron irradiated

4 - Current rating (25 = 25 A)

5 - PB = TO-247AC modified

6 - Voltage rating: (60 = 600 V)

7 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

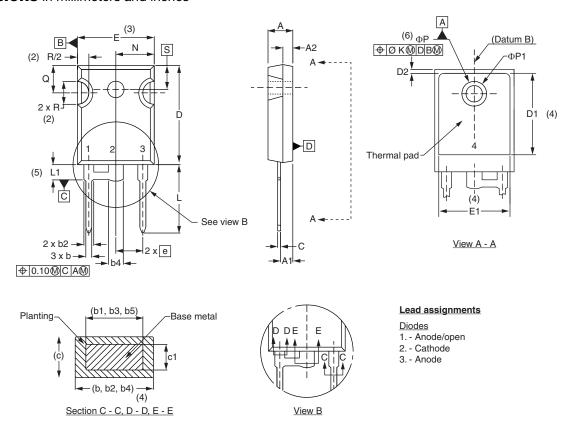
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA25PB60PbF	25	500	Antistatic plastic tube				
VS-HFA25PB60-N3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS						
Dimensions		www.vishay.com/doc?95253				
Dort marking information	TO-247AC modified PbF	www.vishay.com/doc?95255				
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442				



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DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.37	0.065	0.094	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.86	0.015	0.034	
c1	0.38	0.76	0.015	0.030	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIMETERS INCHES		HES	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.72	-	0.540	-	
е	5.46	BSC	0.215	BSC	
ΦК	2.	54	0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62 BSC		0	.3	
ΦР	3.56	3.66	0.14	0.144	
ФР1	1	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	1.78	0.216	
S	5.51	BSC	0.217	BSC	

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) ΦP to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



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